L	Hits	Search Text	DB	Time stamp
Number 1	644	compensat\$5 near mask	USPAT; US-PGPUB;	2004/02/23 05:14
2	6	(compensat\$5 near mask) and (main near mask)	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/02/23 05:17
3	2	mami near miyasaka	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/02/23 05:19
4	214	(compensat\$5 near mask) and (electron or charged-particle or (charged adj particle))	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/23 05:20
5	73	((compensat\$5 near mask) and (electron or charged-particle or (charged adj particle))) and stage	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/23 05:20
6	22	(((compensat\$5 near mask) and (electron or charged-particle or (charged adj particle))) and stage) and ((second or two or auxiliary or auxilliary) near	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/23 05:33
7	576714	<pre>mask) (electron or charged-particle or (charged adj particle))</pre>	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/23 05:34
8	97280	((electron or charged-particle or (charged adj particle))) and stage	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/23 05:34
9	21650	(((electron or charged-particle or (charged adj particle))) and stage) and mask	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/23 05:34
10	10268	((((electron or charged-particle or (charged adj particle))) and stage) and mask) and exposure	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/23 05:34
11	2035	(((((electron or charged-particle or (charged adj particle))) and stage) and mask) and exposure) and ((plurality or multiple or two or several) near4 mask)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/23 05:35
12	204	(((((electron or charged-particle or (charged adj particle))) and stage) and mask) and exposure) and (compensat\$5 near4 mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/23 05:36
13	58	((((((electron or charged-particle or (charged adj particle))) and stage) and mask) and exposure) and (compensat\$5 near4 mask)) and defect\$5	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/23 05:36
14	55	<pre>(((((((electron or charged-particle or (charged adj particle))) and stage) and mask) and exposure) and (compensat\$5 near4 mask)) and defect\$5) and (substrate or wafer)</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/23 05:37

Search History

2/23/04 6:53:12 AM

			T	10004/00/00
15	54	(((((((electron or charged-particle or	USPAT;	2004/02/23
		(charged adj particle))) and stage) and	US-PGPUB;	05:37
		mask) and exposure) and (compensat\$5	EPO; JPO;	
		near4 mask)) and defect\$5) and	DERWENT;	
		(substrate or wafer)) and (resist or	IBM_TDB	
		photoresist or film)		
16	25	<pre>(((((((((electron or charged-particle or</pre>	USPAT;	2004/02/23
		(charged adj particle))) and stage) and	US-PGPUB;	06:10
		mask) and exposure) and (compensat\$5	EPO; JPO;	
		near4 mask)) and defect\$5) and	DERWENT;	
		(substrate or wafer)) and (resist or	IBM TDB	
		photoresist or film)) and lens and	_	
		deflect\$4		
17	4	5888682.URPN.	USPAT	2004/02/23
				05:42
20	3	((compensation adj mask) and	USPAT;	2004/02/23
!		(charged-particle or (charged adj	US-PGPUB;	06:10
		particle) or electron)) and (stage near2	EPO; JPO;	
		mask)	DERWENT;	
			IBM TDB	
19	31	(compensation adj mask) and	USPAT;	2004/02/23
		(charged-particle or (charged adj	US-PGPUB;	06:11
		particle) or electron)	EPO; JPO;	
			DERWENT;	
			IBM TDB]
21	2	("5254438" "5316879").PN.	USPAT	2004/02/23
		, , ,		06:15
18	99	compensation adj mask	USPAT;	2004/02/23
~~			US-PGPUB;	06:26
			EPO; JPO;	
			DERWENT;	
			IBM TDB	

Hits Search Text Number 339 auxiliary near mask USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB 2 94 (auxiliary near mask) and (electron or USPAT; DB Time star	2.3
US-PGPUB; 08:03 EPO; JPO; DERWENT; IBM_TDB 2 94 (auxiliary near mask) and (electron or USPAT; 2004/02/2	
EPO; JPO; DERWENT; IBM_TDB 2 94 (auxiliary near mask) and (electron or USPAT; 2004/02/2	23
DERWENT; IBM_TDB 2 94 (auxiliary near mask) and (electron or USPAT; 2004/02/2	23
IBM_TDB 2 94 (auxiliary near mask) and (electron or USPAT; 2004/02/2	23
2 94 (auxiliary near mask) and (electron or USPAT; 2004/02/2	23
abancad mantial and tabancad add	
charged-particle or (charged adj US-PGPUB; 08:04	
particle))	
DERWENT; IBM TDB	
3 42 ((auxiliary near mask) and (electron or USPAT; 2004/02/2	23
charged-particle or (charged adj US-PGPUB; 08:04	
particle))) and stage EPO; JPO;	
DERWENT;	
IBM_TDB	
12 (((auxiliary near mask) and (electron or USPAT; 2004/02/2 charged-particle or (charged adj US-PGPUB; 09:08	23
particle))) and stage) and compensat\$5 EPO; JPO;	
DERWENT;	
IBM_TDB	
5 10268 (electron or charged-particle or (charged USPAT; 2004/02/2	23
adj particle)) and exposure and mask and US-PGPUB; 09:09	
stage EPO; JPO; DERWENT;	
IBM TDB	
6 3176 ((electron or charged-particle or USPAT; 2004/02/2	23
(charged adj particle)) and exposure and US-PGPUB; 09:09	
mask and stage) and ((wafer or substrate) EPO; JPO;	
near4 stage) DERWENT; IBM TDB	
7 1277 (((electron or charged-particle or USPAT; 2004/02/2	23
(charged adj particle)) and exposure and US-PGPUB; 09:10	
mask and stage) and ((wafer or substrate) EPO; JPO;	
near4 stage)) and ((mask or reticle or DERWENT;	
rectile) near4 stage) 1BM_TDB	7
(charged adj particle)) and exposure and US-PGPUB; 09:11	
mask and stage) and ((wafer or substrate) EPO; JPO;	
near4 stage)) and ((mask or reticle or DERWENT;	
rectile) near4 stage)) and ((plurality or IBM_TDB	
several or multiple or two) near4 (mask or rectile or reticle))	
9 854 ((((electron or charged-particle or USPAT; 2004/02/2	23
(charged adj particle)) and exposure and US-PGPUB; 09:11	
mask and stage) and ((wafer or substrate) EPO; JPO;	
near4 stage)) and ((mask or reticle or DERWENT; rectile) near4 stage)) and ((plurality or IBM TDB	
several or multiple or two or second)	
near4 (mask or rectile or reticle))	
10 754 ((((electron or charged-particle or USPAT; 2004/02/2	23
(charged adj particle)) and exposure and US-PGPUB; 09:12	
mask and stage) and ((wafer or substrate) EPO; JPO; near4 stage)) and ((mask or reticle or DERWENT;	
rectile) near4 stage)) and ((plurality or IBM TDB	
several or multiple or two or second)	
near4 (mask or rectile or reticle))) and	
(resist or photoresist)	2
361 ((((((electron or charged-particle or USPAT; 2004/02/2 (charged adj particle)) and exposure and US-PGPUB; 09:13	.3
mask and stage) and ((wafer or substrate) EPO; JPO;	
near4 stage)) and ((mask or reticle or DERWENT;	
rectile) near4 stage)) and ((plurality or IBM_TDB	
several or multiple or two or second)	
near4 (mask or rectile or reticle))) and (resist or photoresist)) and stor\$4 and	
(location or position or address\$2)	

12	354	<pre>(((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage) and ((wafer or substrate) near4 stage)) and ((mask or reticle or rectile) near4 stage)) and ((plurality or several or multiple or two or second) near4 (mask or rectile or reticle))) and (resist or photoresist)) and stor\$4 and (location or position or address\$2)) and control\$5</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23
13	325	<pre>(((((((((electron or charged-particle or (charged adj particle)) and exposure and mask and stage) and ((wafer or substrate) near4 stage)) and ((mask or reticle or rectile) near4 stage)) and ((plurality or several or multiple or two or second) near4 (mask or rectile or reticle))) and (resist or photoresist)) and stor\$4 and (location or position or address\$2)) and control\$5) and lens</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23
14	98	<pre>((((((((((((((((((((((((((((((((((((</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 09:14
15	6	<pre>((((((((((((((((((((((((((((((((((((</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23
16	49		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23
17	108	compensation adj (mask or reticle or rectile)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/23 09:56
18	34	(compensation adj (mask or reticle or rectile)) and (electron or charged-particle or (charged adj particle))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23
19	20	((compensation adj (mask or reticle or rectile)) and (electron or charged-particle or (charged adj particle))) and exposure	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/23 09:57
20	1030	(electron or charged-particle or (charged adj particle)) and ((wafer or substrate) near stage) and ((reticle or rectile or mask) near stage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2004/02/23 10:02

				10001100
21	245	((electron or charged-particle or	USPAT;	2004/02/23
		(charged adj particle)) and ((wafer or	US-PGPUB;	10:17
		substrate) near stage) and ((reticle or	EPO; JPO;	
		rectile or mask) near stage)) and ((two	DERWENT;	
		or second) near (mask or reticle or	IBM_TDB	
		rectile))		
22	1587	((two or second) near (mask or reticle	USPAT;	2004/02/23
		or rectile)) and ((correct\$4 or	US-PGPUB;	10:19
		reference) near2 (mask or reticle or	EPO; JPO;	
		rectile))	DERWENT;	
			IBM_TDB] , , ,
23	11	1 ' ''	USPAT;	2004/02/23
		or rectile)) and ((correct\$4 or	US-PGPUB;	10:21
		reference) near2 (mask or reticle or	EPO; JPO;	
	į į	rectile))) and (non-defective)	DERWENT;	
			IBM_TDB	
24	2512	((two or second) near (mask or reticle or	USPAT;	2004/02/23
		rectile)) and exposure and (electron or	US-PGPUB;	10:36
		charged-particle or (charged adj	EPO; JPO;	
		particle))	DERWENT;	
			IBM TDB	
25	396	(((two or second) near (mask or reticle	USPAT;	2004/02/23
		or rectile)) and exposure and (electron	US-PGPUB;	10:37
		or charged-particle or (charged adj	EPO; JPO;	
		particle))) and ((wafer or sample or	DERWENT;	
		substrate) near stage)	IBM TDB	
26	245	((((two or second) near (mask or reticle	USPĀT;	2004/02/23
		or rectile)) and exposure and (electron	US-PGPUB;	10:38
		or charged-particle or (charged adj	EPO; JPO;	
		particle))) and ((wafer or sample or	DERWENT;	
		substrate) near stage)) and ((mask or	IBM TDB	
		rectile or reticle) near stage)	_	
27	220	((((two or second) near (mask or reticle	USPAT;	2004/02/23
		or rectile)) and exposure and (electron	US-PGPUB;	10:39
		or charged-particle or (charged adj	EPO; JPO;	
		particle))) and ((wafer or sample or	DERWENT;	
		substrate) near stage)) and ((mask or	IBM TDB	
		rectile or reticle) near stage)) and	_	1
		((electron or charged-particle or		
		(charged adj particle)) near beam)		•
28	193	(((((two or second) near (mask or	USPAT;	2004/02/23
		reticle or rectile)) and exposure and	US-PGPUB;	10:40
		(electron or charged-particle or (charged		
		adj particle))) and ((wafer or sample or	DERWENT;	
		substrate) near stage)) and ((mask or	IBM TDB	
		rectile or reticle) near stage)) and	_	
		((electron or charged-particle or		
		(charged adj particle)) near beam)) and		
		((resist or photoresist or film) with		
		(substrate or wafer or sample))		
29	185	((((((two or second) near (mask or	USPAT;	2004/02/23
		reticle or rectile)) and exposure and	US-PGPUB;	10:40
		(electron or charged-particle or (charged	EPO; JPO;	
		adj particle))) and ((wafer or sample or	DERWENT;	
		substrate) near stage)) and ((mask or	IBM TDB	
		rectile or reticle) near stage)) and	_	
		((electron or charged-particle or		
		(charged adj particle)) near beam)) and		
		((resist or photoresist or film) with		
	×	(substrate or wafer or sample))) and		
		(lens or (electron near optic\$3))		
	L	1 /=		·

30	178	<pre>(((((((((two or second) near (mask or reticle or rectile)) and exposure and (electron or charged-particle or (charged adj particle))) and ((wafer or sample or substrate)near stage)) and ((mask or rectile or reticle) near stage)) and ((electron or charged-particle or (charged adj particle)) near beam)) and ((resist or photoresist or film) with (substrate or wafer or sample))) and (lens or (electron near optic\$3))) and control\$4</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 10:41
31	58	·	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/23 10:41